Bi-Directional N-Channel 20-V (D-S) MOSFET

CHARACTERISTICS

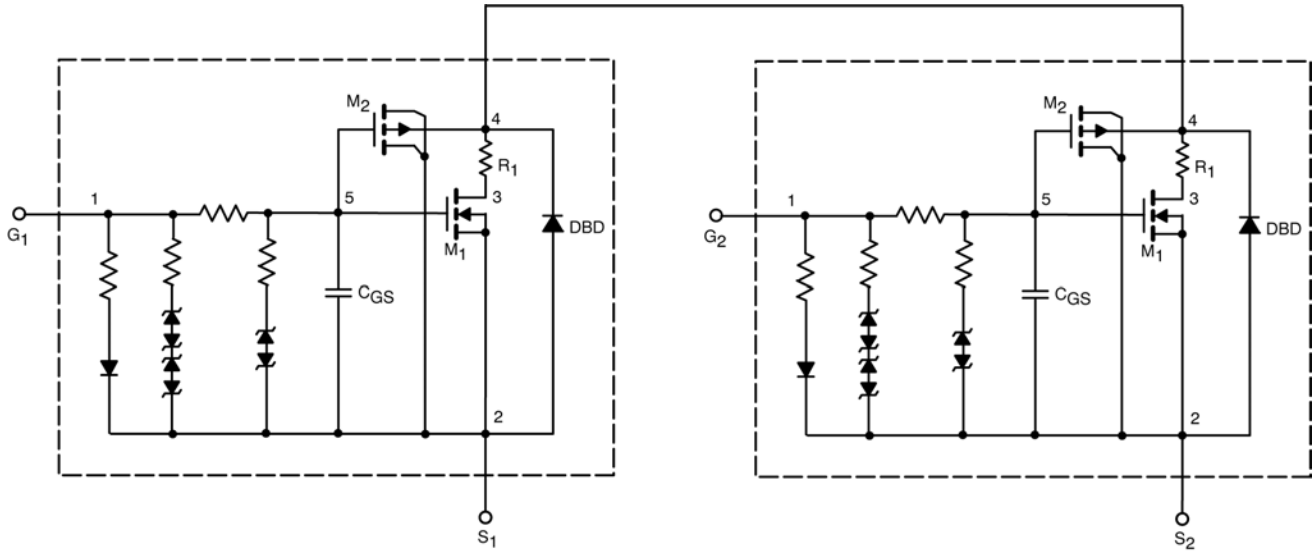
- N-Channel Vertical DMOS
- Macro Model (Subcircuit Model)
- Level 3 MOS
- Apply for both Linear and Switching Application
- Accurate over the −55 to 125°C Temperature Range
- Model the Gate Charge, Transient, and Diode Reverse Recovery Characteristics

DESCRIPTION

The attached spice model describes the typical electrical characteristics of the n-channel vertical DMOS. The subcircuit model is extracted and optimized over the −55 to 125°C temperature ranges under the pulsed 0-V to 5-V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched C_{gd} model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

SUBCIRCUIT MODEL SCHEMATIC

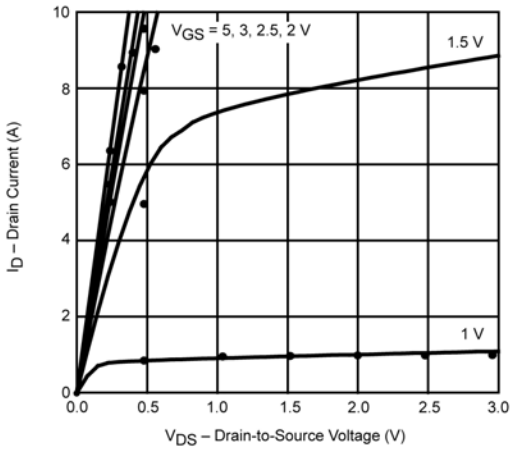


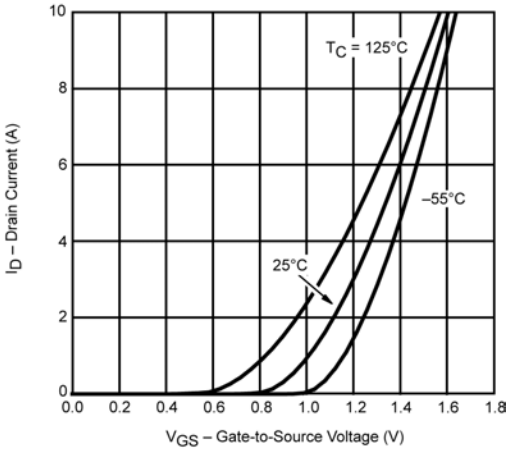
This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.

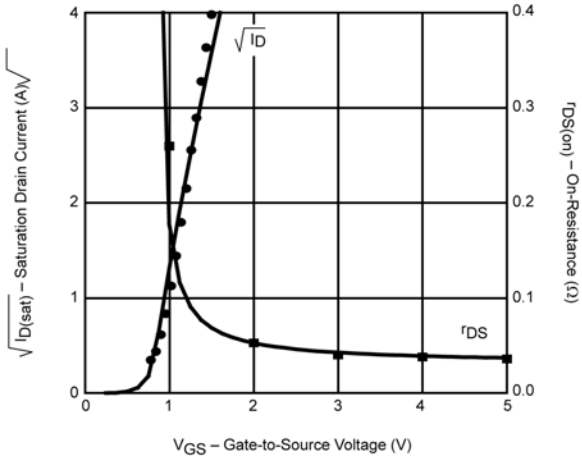
SPECIFICATIONS (T_J = 25°C UNLESS OTHERWISE NOTED)					
Parameter	**Symbol**	**Test Condition**	**Simulated Data**	**Measured Data**	**Unit**
Static					
Gate Threshold Voltage	$V_{GS(th)}$	V_{sS} = V_{GS}, I_D = 250 µA	0.51		V
On-State Drain Current[a]	$I_{ss(on)}$	V_{sS} = 5 V, V_{GS} = 4.5 V	109		A
Drain-Source On-State Resistance[a]	$R_{sS(on)}$	V_{GS} = 4.5 V, I_{ss} = 1 A	0.038	0.038	Ω
		V_{GS} = 3.7 V, I_{ss} = 1 A	0.040	0.041	
		V_{GS} = 2.5 V, I_{ss} = 1 A	0.046	0.048	
		V_{GS} = 1.8 V, I_{ss} = 1 A	0.057	0.060	
Forward Transconductance[a]	g_{fs}	V_{sS} = 10 V, I_{SS}= 1 A	11	20	S
Dynamic[b]					
Turn-On Delay Time	$t_{d(on)}$	V_{ss} = 10 V, R_L = 10 Ω I_{ss} ≅ 1 A, V_{GEN} = 4.5 V, R_G = 6 Ω	4	1	µs
Rise Time	t_r		2	3	
Turn-Off Delay Time	$t_{d(off)}$		7	17	
Fall Time	t_f		4	10	

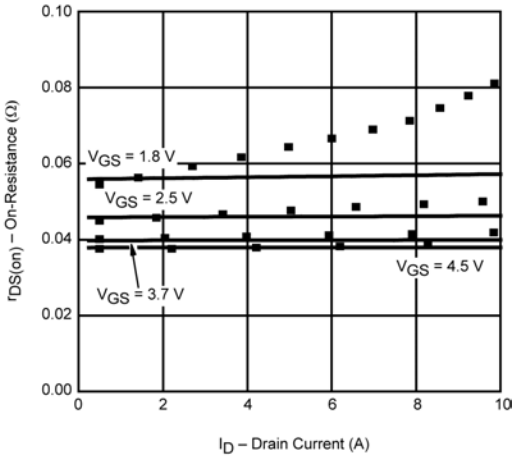
Notes
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2%.
b. Guaranteed by design, not subject to production testing.

COMPARISON OF MODEL WITH MEASURED DATA (T_J=25°C UNLESS OTHERWISE NOTED)









Note: Dots and squares represent measured data.

Disclaimer

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